LOW-POWER CLOCKED FIRST-IN, FIRST-OUT MEMORY

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DL PACKAGE

- Member of the Texas Instruments Widebus™ Family
- Low-Power Advanced CMOS Technology
- Operates From 3-V to 3.6-V V_{CC}
- Free-Running Read and Write Clocks Can Be Asynchronous or Coincident
- Read and Write Operations Synchronized to Independent System Clocks
- Half-Full Flag and Programmable Almost-Full/Almost-Empty Flag
- Bidirectional Configuration and Width Expansion Without Additional Logic
- Input-Ready Flag Synchronized to Write Clock
- Output-Ready Flag Synchronized to Read Clock
- Fast Access Times of 13 ns With a 50-pF Load and All Data Outputs Switching Simultaneously
- Data Rates up to 50 MHz
- Pin-to-Pin Compatible With SN74ACT7803, SN74ACT7805, and SN74ACT7813
- Packaged in Shrink Small-Outline 300-mil Package Using 25-mil Center-to-Center Lead Spacing

description

The SN74ALVC7813 is suited for buffering asynchronous data paths up to 50-MHz clock rates and 13-ns access times. This device is designed for 3-V to 3.6-V $V_{\rm CC}$ operation. Two devices can be configured for bidirectional data buffering without additional logic.

(TOP VIEW) RESET [56 OE1 D17 1 2 55 Q17 D16 **∏**3 54 \ Q16 D15 **∏**4 53 **∏** Q15 D14 ¶5 52 | GND D13 **∏**6 51 Q14 D12 17 50 VCC D11 Π8 49 **□** Q13 D10 **[**] 9 48 Q12 V_{CC} 10 47 N Q11 D9 11 46 Q10 45 DQ9 D8 **1**12 GND **1** 13 44 GND 43 **∏** Q8 D7 **∏** 14 D6 **1**5 42 Q7 D5 **∏** 16 41 **∏** Q6 D4 **∏** 17 40 **□** Q5 D3 **1** 18 39 V_{CC} D2 **1**19 38 \ Q4 D1 **∏**20 37 **∏** Q3 D0 **1**21 36 ∏ Q2 HF **1**22 35 GND PEN 23 34 \ Q1 33 D Q0 AF/AE **1**24 WRTCLK [] 25 32 RDCLK WRTEN2 26 31 RDEN WRTEN1 **1**27 30 OE2 29 OR IR **∏** 28

The write clock (WRTCLK) and read clock (RDCLK) are free running and can be asynchronous or coincident. Data is written to memory on the rising edge of WRTCLK when WRTEN1 is high, WRTEN2 is low, and input ready (IR) is high. Data is read from memory on the rising edge of RDCLK when RDEN, OE1, and OE2 are low and output ready (OR) is high. The first word written to memory is clocked through to the output buffer, regardless of the RDEN, OE1, and OE2 levels. The OR flag indicates that valid data is present on the output buffer.

The FIFO can be reset asynchronously to WRTCLK and RDCLK. Reset (RESET) must be asserted while at least four WRTCLK and four RDCLK rising edges occur to clear the synchronizing registers. Resetting the FIFO initializes the IR, OR, and half-full (HF) flags low and the almost-full/almost-empty (AF/AE) flag high. The FIFO must be reset upon power up.

The SN74ALVC7813 is characterized for operation from 0°C to 70°C.



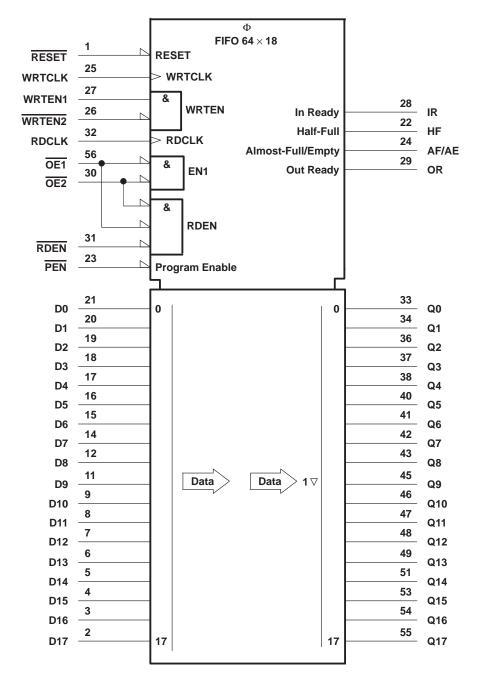
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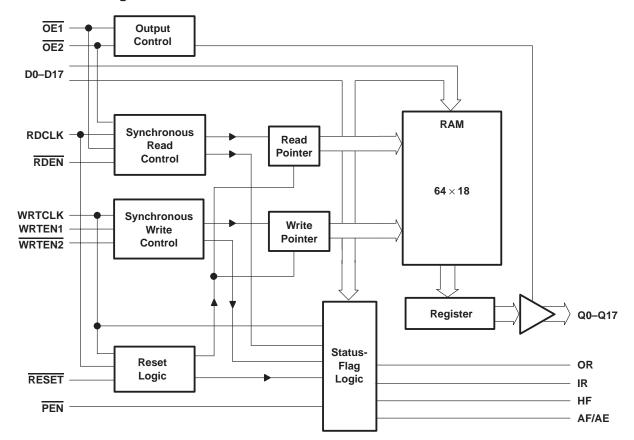
logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



functional block diagram



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Terminal Functions

TERMINAL			
NAME	NO.	1/0	DESCRIPTION
AF/AE	24	0	Almost-full/almost-empty flag. Depth-offset values can be programmed for this flag, or the default value of 8 can be used for both the almost-empty offset (X) and the almost-full offset (Y). AF/AE is high when memory contains X or fewer words or $(64 - Y)$ or more words. AF/AE is high after reset.
D0-D17	2–9, 11–12, 14–21	_	18-bit data input port
HF	22	0	Half-full flag. HF is high when the FIFO memory contains 32 or more words. HF is low after reset.
IR	28	0	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is low during reset and goes high on the second low-to-high transition of WRTCLK after reset.
OE1 OE2	56 30	ı	Output enables. When OE1, OE2, and RDEN are low and OR is high, data is read from the FIFO on a low-to-high transition of RDCLK. When either OE1 or OE2 is high, reads are disabled and the data outputs are in the high-impedance state.
OR	29	0	Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on Q0–Q17 when OR is high. OR is low during reset and goes high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
PEN	23	I	Program enable. After reset and before the <u>first</u> word is written to the FIFO, the binary value on D0–D7 is latched as an AF/AE offset value when <u>PEN</u> is low and WRTCLK is high.
Q0-Q17	33–34, 36–38, 40–43, 45–49, 51, 53–55	0	18-bit data output port. After the first valid write to empty memory, the first word is output on Q0–Q17 on the third rising edge of RDCLK. OR also is asserted high at this time to indicate ready data. When OR is low, the last word read from the FIFO is present on Q0–Q17.
RDCLK	32	I	Read clock. RDCLK is a continuous clock and can be asynchronous or coincident to WRTCLK. A low-to-high transition of RDCLK reads data from memory when OE1, OE2, and RDEN are low and OR is high. OR is synchronous to the low-to-high transition or RDCLK.
RDEN	31	I	Read enable. When RDEN, OE1, and OE2 are low and OR is high, data is read from the FIFO on the low-to-high transition of RDCLK.
RESET	1	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while RESET is low. This sets HF, IR, and OR low and AF/AE high.
WRTCLK	25	I	Write clock. WRTCLK is a continuous clock and can be asynchronous or coincident to RDCLK. A low-to-high transition of WRTCLK writes data to memory when WRTEN2 is low, WRTEN1 is high, and IR is high. IR is synchronous to the low-to-high transition of WRTCLK.
WRTEN1 WRTEN2	27 26	I	Write enables. When WRTEN1 is high, WRTEN2 is low, and IR is high, data is written to the FIFO on a low-to-high transition of WRTCLK.





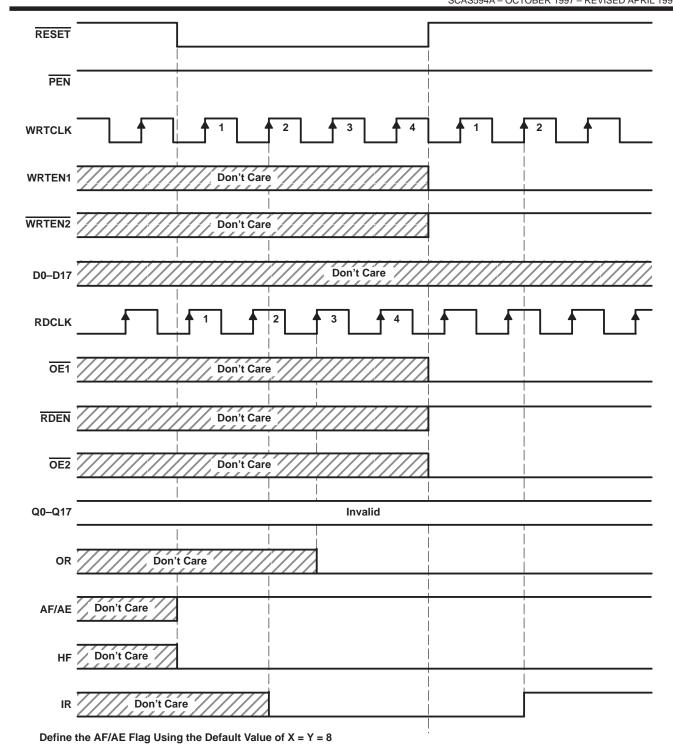
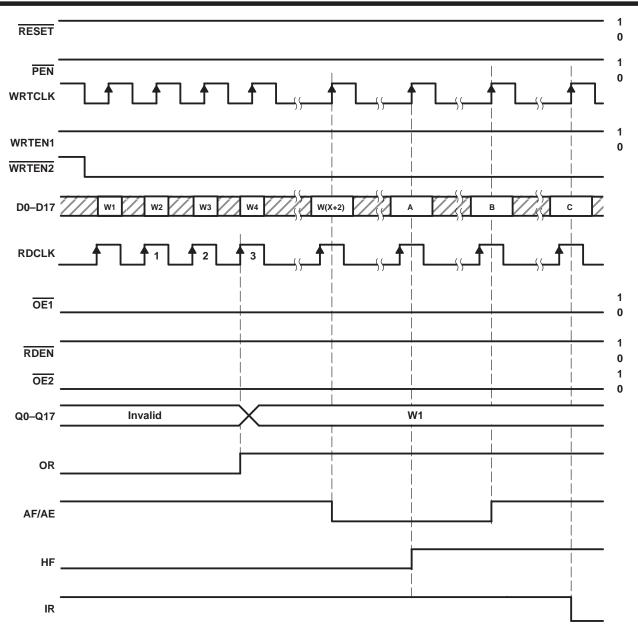


Figure 1. Reset Cycle





DATA-WORD NUMBER FOR FLAG TRANSITIONS

DEVICE	TRA	TRANSITION WORD					
DEVICE	Α	В	С				
SN74ALVC7813	W33	W(65 – Y)	W65				

Figure 2. FIFO Write



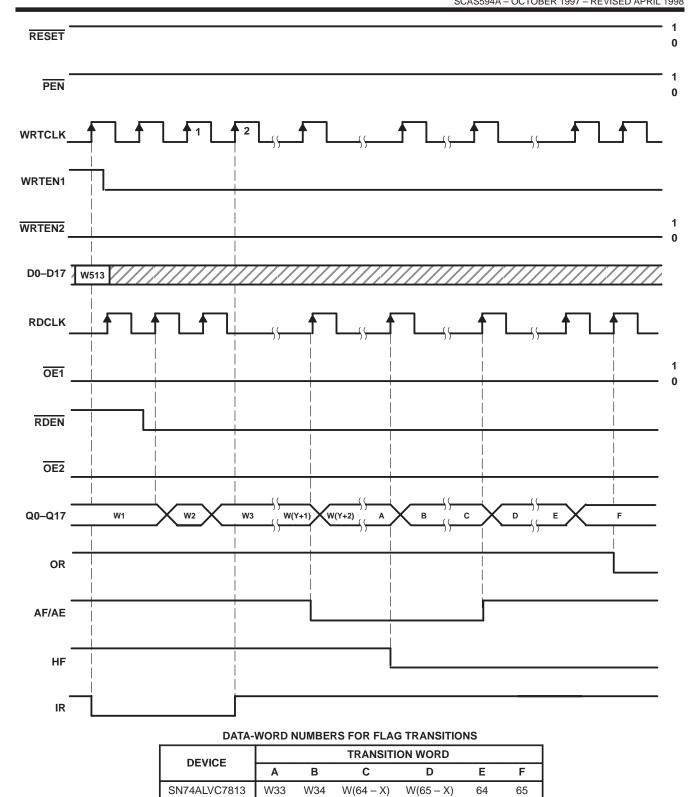


Figure 3. FIFO Read



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offset values for AF/AE

The AF/AE flag has two programmable limits: the almost-empty offset value (X) and the almost-full offset value (Y). They can be programmed after the FIFO is reset and before the first word is written to memory. If the offsets are not programmed, the default values of X = Y = 8 are used. The AF/AE flag is high when the FIFO contains X or fewer words or (64 - Y) or more words.

Program enable (\overline{PEN}) should be held high throughout the reset cycle. \overline{PEN} can be brought low only when IR is high. On the following low-to-high transition of WRTCLK, the binary value on D0–D7 is stored as the almost-empty offset value (X) and the almost-full offset value (Y). Holding \overline{PEN} low for another low-to-high transition of WRTCLK reprograms Y to the binary value on D0–D7 at the time of the second WRTCLK low-to-high transition. When the offsets are being programmed, writes to the FIFO memory are disabled, regardless of the state of the write enables (WRTEN1, $\overline{WRTEN2}$). A maximum value of 63 can be programmed for either X or Y (see Figure 4). To use the default values of X = Y = 8, \overline{PEN} must be held high.

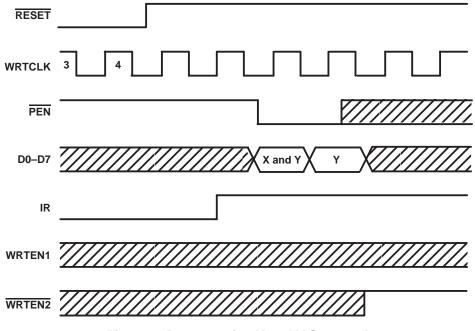


Figure 4. Programming X and Y Separately



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	–0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V _O (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Voltage range applied to a disabled 3-state output	–0.5 V to 3.6 V
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3)	74°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings can be exceeded if the input and output clamp current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			'ALVC7	'ALVC7813-20		'ALVC7813-25		'ALVC7813-40		
			MIN	MAX	MIN	MAX	MIN	MAX	UNIT	
Vcc	Supply voltage		3	3.6	3	3.6	3	3.6	V	
VIH	High-level input voltage				2		2		V	
VIL	Low-level input voltage			0.8		0.8		0.8	V	
ІОН	High-level output current, Q outputs, flags	V _{CC} = 3 V		-8		-8		-8	mA	
loL	Low-level output current, Q outputs, flags	V _{CC} = 3 V		16		16		16	mA	
TA	Operating free-air temperature		0	70	0	70	0	70	°C	

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

F	PARAMETER	TEST CONDITIONS		MIN	TYP‡	MAX	UNIT
VIK		V _{CC} = 3 V,	$I_{IK} = -18 \text{ mA}$			-1.2	V
Vall	Flags, Q outputs	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	I _{OH} = -100 μA	V _{CC} -0.2	2		V
VOH	riags, & outputs	V _{CC} = 3 V,	$I_{OH} = -8 \text{ mA}$	2.4			V
	Flags, Q outputs	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$	$I_{OL} = 100 \mu\text{A}$			0.2	
VOL	Flags	V _{CC} = 3 V,	I _{OL} = 8 mA			0.4	V
	Q outputs	V _{CC} = 3 V,	I _{OL} = 16 mA			0.55	
Ц		V _{CC} = 3.6 V,	$V_I = V_{CC}$ or GND			±5	μΑ
loz		$V_{CC} = 3.6 \text{ V},$	$V_O = V_{CC}$ or GND			±10	μΑ
Icc		$V_I = V_{CC}$ or 0				40	μΑ
Δlcc§		V _{CC} = 3.6 V, One input at	V _{CC} – 0.6 V, Other inputs at V _{CC} or GND			500	μΑ
Ci		V _{CC} = 3.3 V,	$V_I = V_{CC}$ or GND		2.5		pF
Co		V _{CC} = 3.3 V,	$V_O = V_{CC}$ or GND		5.5		pF

[‡] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



[§] This is the supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or VCC.

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timing requirements over recommended operating conditions (see Figures 1 through 5)

			'ALVC7813-20		'ALVC78	313-25	'ALVC7813-40		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	UNII
fclock	Clock frequency			50		40		25	MHz
		D0-D17 high or low	9		10		14		
		WRTCLK high or low	7		8		12		
		RDCLK high or low	7		8		12		
t _W	Pulse duration	PEN low	9		9		12		ns
		WRTEN1 high, WRTEN2 low	8		8		12		
		OE1, OE2 low	9		9		12		
		RDEN low	8		8		12		
	Setup time	D0–D17 before WRTCLK↑	5		5		5		ns
		WRTEN1, WRTEN2 before WRTCLK↑	5		5		5		
		OE1, OE2 before RDCLK↑	5		6		6		
t _{su}		RDEN before RDCLK↑	5		5		7		
		Reset: RESET low before first WRTCLK↑ and RDCLK↑†	6		6		6		
		PEN before WRTCLK↑	6		6		6		
		D0–D17 after WRTCLK↑	0		0		0		
	Hold time	WRTEN1, WRTEN2 after WRTCLK↑	0		0		0		ns
th		OE1, OE2, RDEN after RDCLK↑	0		0		0		
		Reset: RESET low after fourth WRTCLK↑ and RDCLK↑†	2		2		2		
		PEN low after WRTCLK↑	2		2		2		

[†] To permit the clock pulse to be utilized for reset purposes

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 5)

	FROM	то	'ALVC78	813-20	'ALVC7813-25		'ALVC7813-40		
PARAMETER	(OUTPUT) (INPUT)	MIN	MAX	MIN	MAX	MIN	MAX	UNIT	
f _{max}	WRTCLK or RDCLK		50		40		25		MHz
	RDCLK↑	Any Q	4	13	4	15	4	20	
	WRTCLK↑	IR	3	11	3	13	3	15	
t _{pd}	RDCLK↑	OR	3	11	3	13	3	15	ns
	WRTCLK↑	AF/AE	7	19	7	21	7	23	
	RDCLK↑		7	19	7	21	7	23	
^t PLH	WRTCLK↑	HF	7	17	7	19	7	21	ns
^t PHL	RDCLK↑	HF	7	18	7	20	7	22	ns
tPLH	RESET low	AF/AE	2	11	2	13	2	15	ns
t _{PHL}	RESET low	HF	2	12	2	14	2	16	ns
t _{en}	OE1, OE2	Any Q	2	11	2	11	2	14	ns
^t dis	OE1, OE2	Any Q	2	11	2	14	2	14	ns

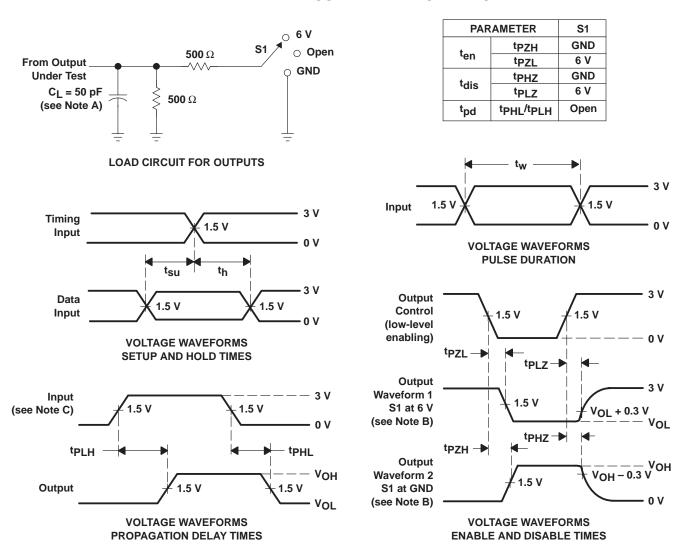
operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

	PARAMETER			TEST CONDITIONS		
C _{pd}	Power dissipation capacitance	Outputs enabled	$C_L = 50 \text{ pF},$	f = 5 MHz	53	pF



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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_{O} = 50 \Omega$, $t_{f} \leq$ 2.5 ns, $t_{f} \leq$ 2.5 ns.

Figure 5. Standard CMOS Outputs (FULL, EMPTY, HF, AF/AE)

TYPICAL CHARACTERISTICS

SUPPLY CURRENT CLOCK FREQUENCY

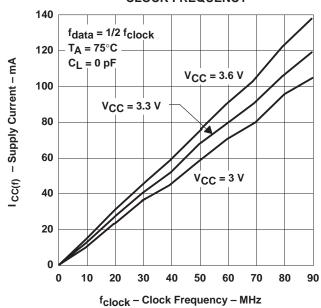


Figure 6

APPLICATION INFORMATION

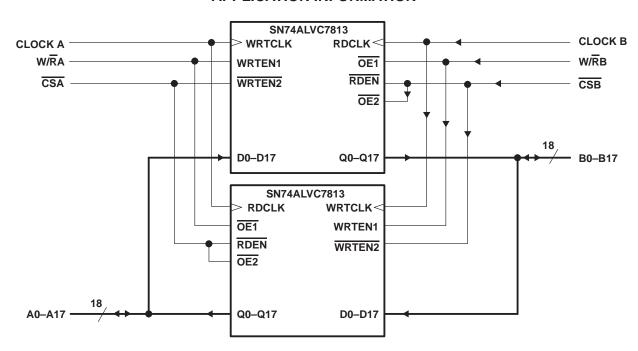


Figure 7. Bidirectional Configuration

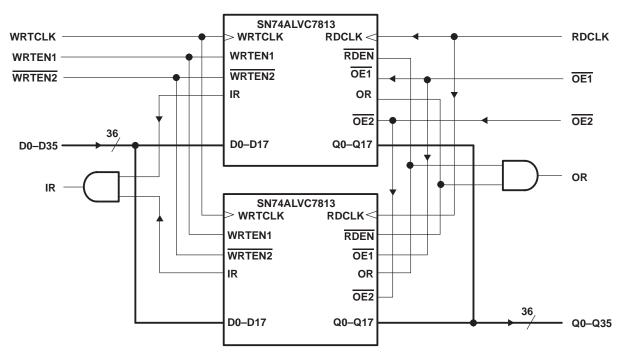


Figure 8. Word-Width Expansion: 64 imes 36 Bits



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